

30 V, 2 A NPN/NPN low VCEsat (BISS) transistor 14 December 2012

Product data sheet

General description 1.

NPN/NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4230PANP. PNP/PNP complement: PBSS5230PAP.

2. **Features and benefits**

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements •
- High efficiency due to less heat generation
- AEC-Q101 qualified

Applications 3.

- Load switch
- Battery-driven devices •
- Power management •
- Charging circuits
- Power switches (e.g. motors, fans)

Quick reference data 4.

Table 1. Quick reference data									
Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V _{CEO}	collector-emitter voltage	open base		-	-	30	V		
I _C	collector current			-	-	2	А		
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	3	А		
Per transistor									
R _{CEsat}	collector-emitter saturation resistance	$\label{eq:loss} \begin{array}{l} {\sf I}_C = 1 \; {\sf A}; \; {\sf I}_B = 0.1 \; {\sf A}; \; {\sf pulsed}; \; {\sf t}_p \leq 300 \; {\sf \mu}{\sf s}; \\ \delta \leq 0.02 \; ; \; {\sf T}_{amb} = 25 \; {}^\circ{\rm C} \end{array}$		-	-	145	mΩ		

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2	1 2 3	E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020-6 (SOT1118)	sym140
7	C1	collector TR1	2	
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information									
Type number	Package								
	Name	Description	Version						
PBSS4230PAN	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body $2 \times 2 \times 0.65$ mm	SOT1118						

7. Marking

	Table 4. Marking codes	
Type number		Marking code
	PBSS4230PAN	2G

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit				
Per transis	Per transistor									
V _{CBO}	collector-base voltage	open emitter		-	30	V				
V _{CEO}	collector-emitter voltage	open base		-	30	V				
V _{EBO}	emitter-base voltage	open collector		-	7	V				
I _C	collector current			-	2	А				
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	А				
I _B	base current			-	0.3	А				
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Symbol	Parameter	Conditions	M	lin Max	Unit
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	370	mW
			[2] -	570	mW
			[3] -	530	mW
			[4] -	700	mW
			[5] -	450	mW
			[6] -	760	mW
			[7] -	700	mW
			[8] -	1450	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	510	mW
			[2] -	780	mW
			[3] -	730	mW
			[4] -	960	mW
			[5] -	620	mW
			[6] -	1040	mW
			[Z] -	960	mW
			[8] -	2000	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature			55 150	°C
T _{stg}	storage temperature			65 150	°C

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.

[4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

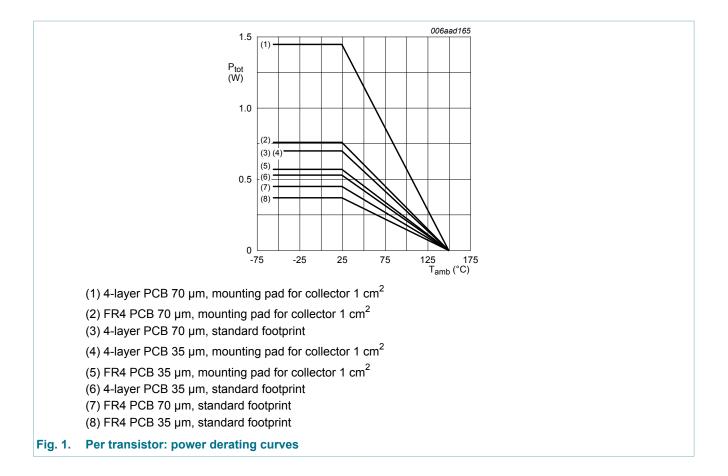
[6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.

[8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

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9. Thermal characteristics

Table 6. T	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	338	K/W
	from junction to		[2]	-	-	219	K/W
	ambient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
			[5]	-	-	278	K/W
			[6]	-	-	164	K/W
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per device							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	245	K/W
	from junction to ambient		[2]	-	-	160	K/W
	ampient		[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.

^[4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

[6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.

[8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

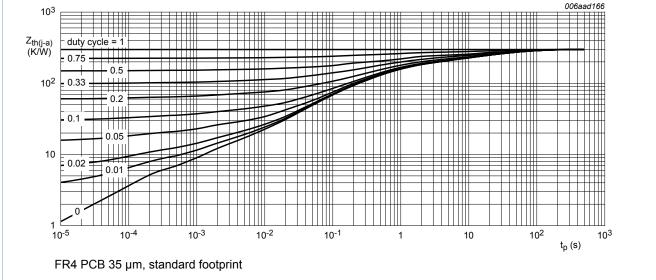
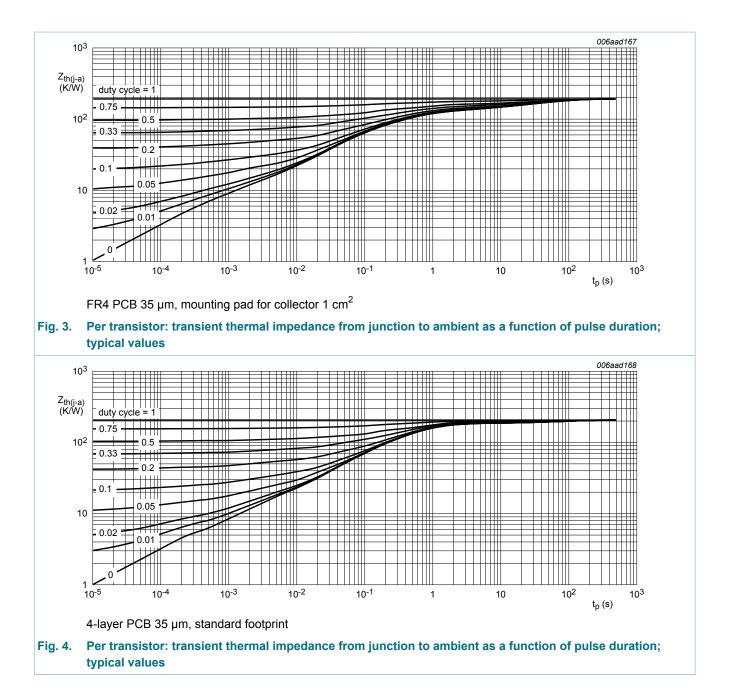


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

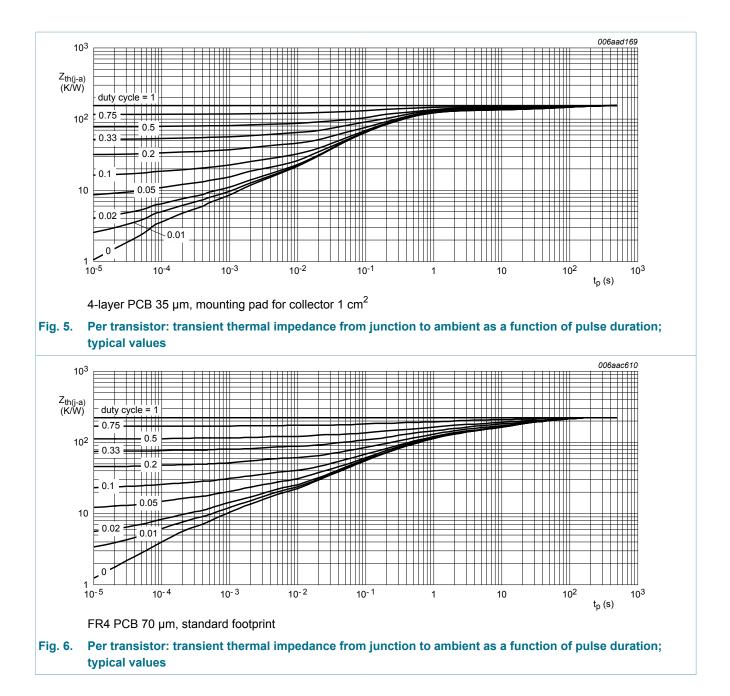


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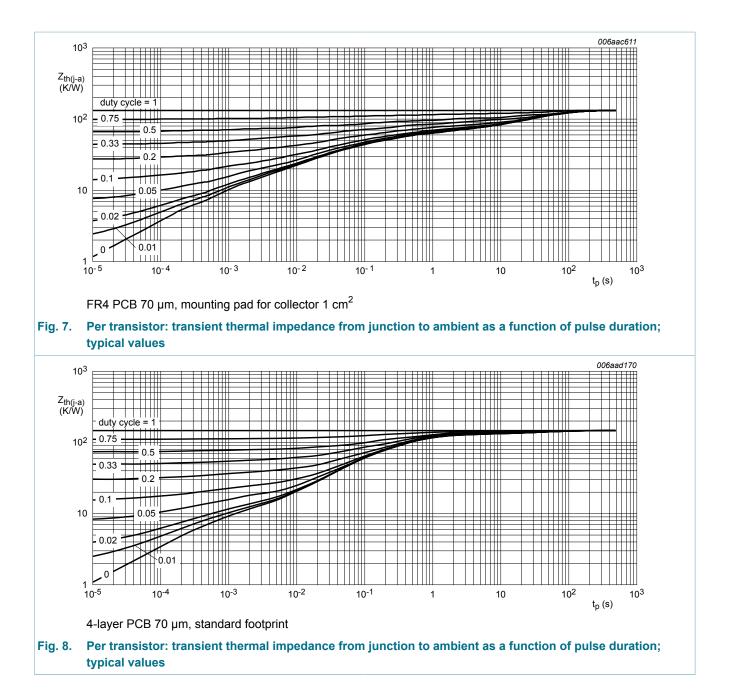
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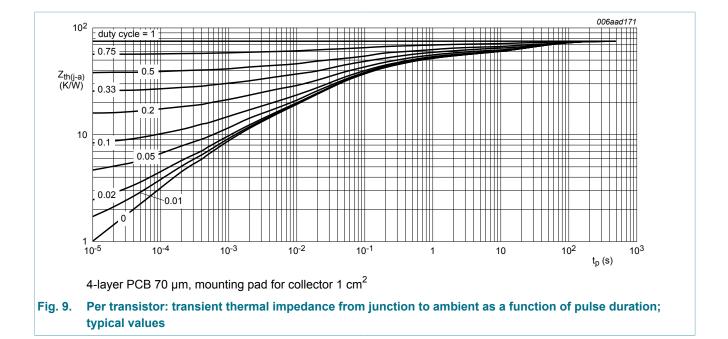


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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor	· · · · ·	I			
I _{CBO}	collector-base cut-off	V _{CB} = 24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 24 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V; } I_C = 100 \text{ mA; pulsed;}$ $t_p \le 300 \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	250	380	-	
		$V_{CE} = 2 \text{ V; } I_C = 500 \text{ mA; pulsed;}$ $t_p \le 300 \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	230	350	-	
		$V_{CE} = 2 \text{ V; } I_C = 1 \text{ A; pulsed; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	200	310	-	
		$V_{CE} = 2 \text{ V; } I_C = 2 \text{ A; pulsed; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	150	230	-	
V _{CEsat}	collector-emitter	I_{C} = 500 mA; I_{B} = 50 mA; T_{amb} = 25 °C	-	60	80	mV
	saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	120	160	mV
		I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	230	300	mV
		I_{C} = 2 A; I_{B} = 200 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	220	290	mV

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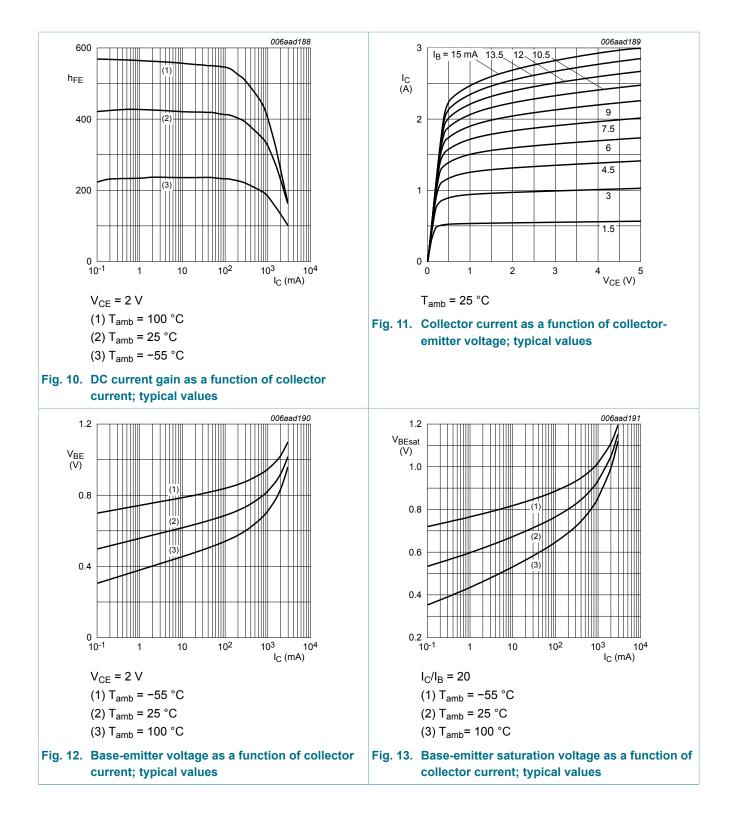
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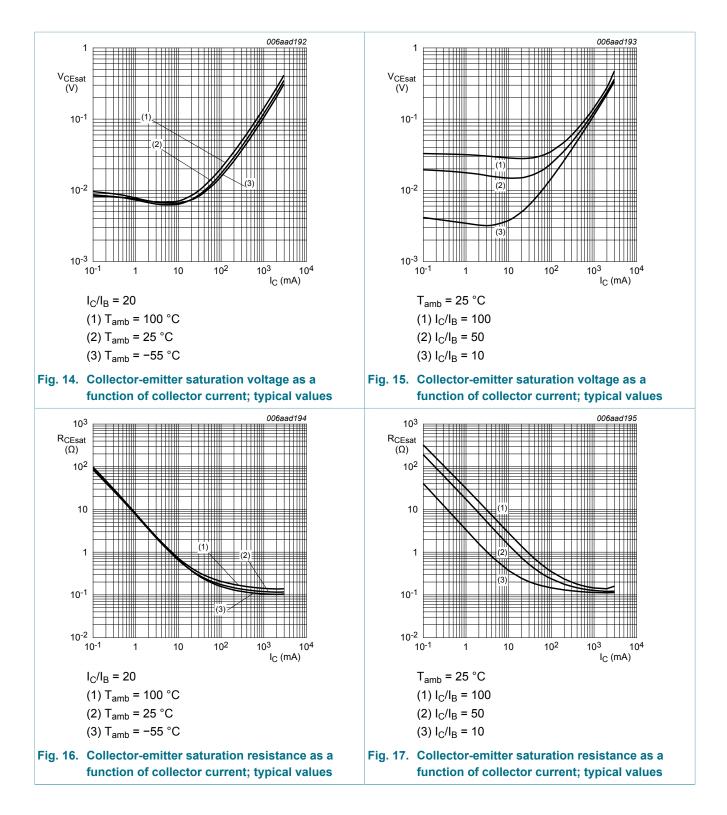
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 1 A; I_{B} = 0.1 A; pulsed; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	145	mΩ
V _{BEsat}	base-emitter saturation	I_{C} = 500 mA; I_{B} = 50 mA; T_{amb} = 25 °C	-	-	1	V
	voltage	I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	1	V
		I_{C} = 2 A; I_{B} = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-	1.1	V
		I_{C} = 2 A; I_{B} = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-	1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I _C = 0.5 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-	0.9	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 50 mA;	-	10	-	ns
t _r	rise time	I _{Boff} = -50 mA; T _{amb} = 25 °C	 -	50	-	ns
t _{on}	turn-on time		 -	60	-	ns
t _s	storage time	-	 -	310	-	ns
t _f	fall time	-	 -	60	-	ns
t _{off}	turn-off time		 -	370	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C	60	120	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	13.5	18	pF

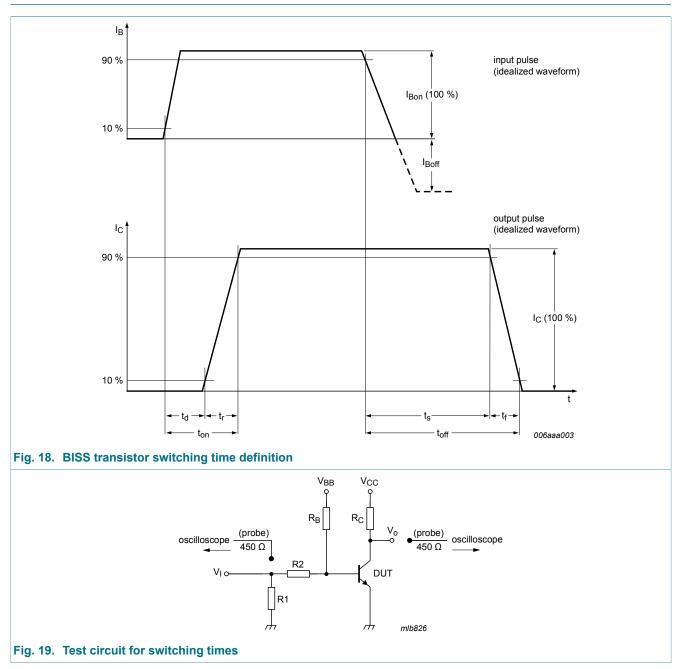
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11. Test information

11.1 Quality information

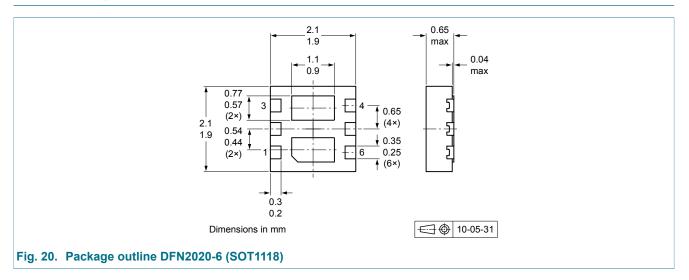
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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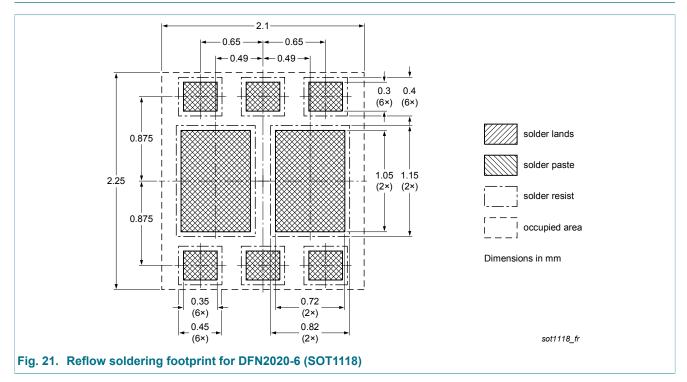
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12. Package outline



13. Soldering



14. Revision history

Table 8. Revision h	istory				
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4230PAN v.1	20121214	Product data sheet	-	-	
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Product data sheet		14 December 2012		14 / 17	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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